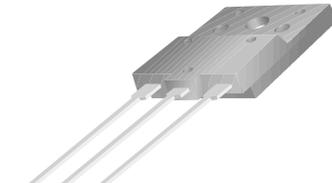


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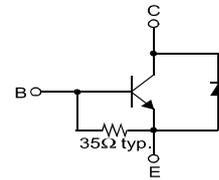
FJAF6810D

High Voltage Color Display Horizontal Deflection Output (Damper Diode Built-In)

- High Collector-Base Breakdown Voltage : $BV_{CBO} = 1500V$
- High Switching Speed : $t_F(\text{typ.}) = 0.1\mu s$
- For Color TV



TO-3PF
1.Base 2.Collector 3.Emmitter
Equivalent Circuit



NPN Triple Diffused Planar Silicon Transistor

Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Rating	Units
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	750	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current (DC)	10	A
I_{CP}^*	Collector Current (Pulse)	20	A
P_C	Collector Dissipation	60	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	-55 ~ 150	$^\circ C$

* Pulse Test: Pulse Width=5ms, Duty Cycle $\leq 10\%$

Electrical Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
I_{CES}	Collector Cut-off Current	$V_{CB} = 1500V, R_{BE} = 0$			1	mA
I_{CBO}	Collector Cut-off Current	$V_{CB} = 800V, I_E = 0$			10	μA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 4V, I_C = 0$	40		250	mA
BV_{EBO}	Base-Emitter Breakdown Voltage	$I_E = 300mA, I_C = 0$	6			V
h_{FE1}	DC Current Gain	$V_{CE} = 5V, I_C = 1A$	7			
h_{FE2}		$V_{CE} = 5V, I_C = 6A$	5		8	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 6A, I_B = 1.5A$			3	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 6A, I_B = 1.5A$			1.5	V
V_F	Damper Diode Turn On Voltage	$I_F = 6A$			2	V
t_{STG}^*	Storage Time	$V_{CC} = 200V, I_C = 6A, R_L = 33\Omega$ $I_{B1} = 1.2A, I_{B2} = -2.4A$			3	μs
t_F^*	Fall Time				0.2	μs

* Pulse Test: PW=20 μs , duty Cycle=1% Pulsed

Thermal Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case		2.08	$^\circ C/W$